



P-Channel 60-V (D-S) 175 °C MOSFET

PRODUCT SUMMARY

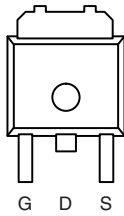
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ)
- 60	0.060 at $V_{GS} = - 10$ V	- 19	26
	0.077 at $V_{GS} = - 4.5$ V	- 16.8	

FEATURES

- TrenchFET[®] Power MOSFET
- 175 °C Junction Temperature

RoHS
COMPLIANT

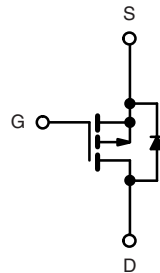
TO-252



Top View

Drain Connected to Tab

Ordering Information: SUD19P06-60L-E3 (Lead (Pb)-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	- 60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 175$ °C)	I_D	$T_C = 25$ °C	- 19
		$T_C = 125$ °C	- 11
Pulsed Drain Current	I_{DM}	- 30	A
Avalanche Current, Single Pulse	I_{AS}	- 22	
Repetitive Avalanche Energy, Single Pulse ^a	E_{AS}	24.2	mJ
Power Dissipation	P_D	$T_C = 25$ °C	46 ^c
		$T_A = 25$ °C	2.7 ^{b, c}
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient ^b	R_{thJA}	$t \leq 10$ s	17	21
		Steady State	45	55
Junction-to-Case	R_{thJC}	2.7	3.25	°C/W

Notes:

- Duty cycle ≤ 1 %.
- When mounted on 1" square PCB (FR-4 material).
- See SOA curve for voltage derating.

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-1		-3	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			-50	
		$V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$			-150	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\text{ V}, V_{GS} = -10\text{ V}$	-30			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -10\text{ A}$		0.048	0.060	Ω
		$V_{GS} = -10\text{ V}, I_D = -16.8\text{ A}, T_J = 125\text{ }^\circ\text{C}$			0.102	
		$V_{GS} = -10\text{ V}, I_D = -16.8\text{ A}, T_J = 175\text{ }^\circ\text{C}$			0.129	
		$V_{GS} = -4.5\text{ V}, I_D = -5\text{ A}$		0.061	0.077	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15\text{ V}, I_D = -10\text{ A}$		22		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = -25\text{ V}, f = 1\text{ MHz}$		1140	1710	pF
Output Capacitance	C_{oss}		130			
Reverse Transfer Capacitance	C_{rss}		90			
Total Gate Charge	Q_g	$V_{DS} = -30\text{ V}, V_{GS} = -10\text{ V}, I_D = -10\text{ A}$		26	40	nC
Gate-Source Charge	Q_{gs}		4.5			
Gate-Drain Charge	Q_{gd}		7.0			
Gate Resistance	R_g	$f = 1\text{ MHz}$		7.0		Ω
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = -30\text{ V}, R_L = 3\text{ }\Omega$ $I_D \cong -19\text{ A}, V_{GEN} = -10\text{ V}, R_g = 2.5\text{ }\Omega$		8	15	ns
Rise Time ^c	t_r		9	15		
Turn-Off Delay Time ^c	$t_{d(off)}$		65	100		
Fall Time ^c	t_f		30	45		
Drain-Source Body Diode Characteristics ($T_C = 25\text{ }^\circ\text{C}$) ^b						
Continuous Current	I_S				-30	A
Pulsed Current	I_{SM}				-30	
Forward Voltage ^a	V_{SD}	$I_F = -19\text{ A}, V_{GS} = 0\text{ V}$		-1.0	-1.5	V
Reverse Recovery Time	t_{rr}	$I_F = -19\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		41	61	ns

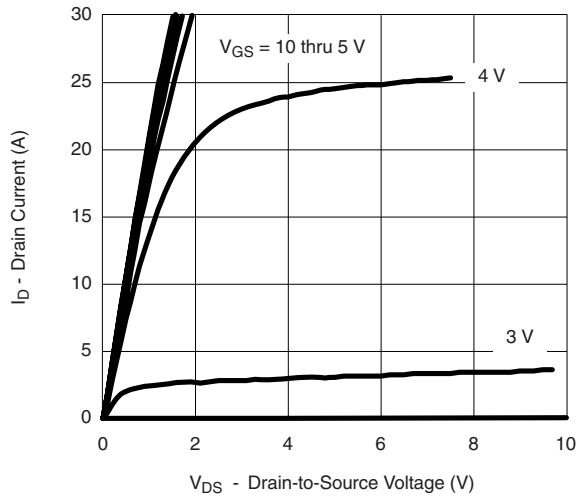
Notes:

- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

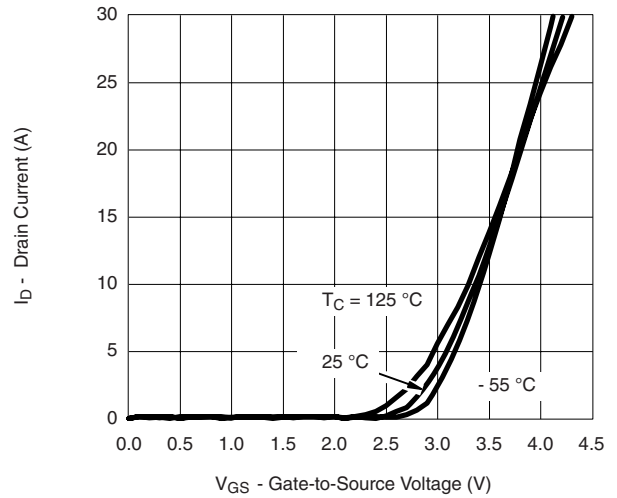
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



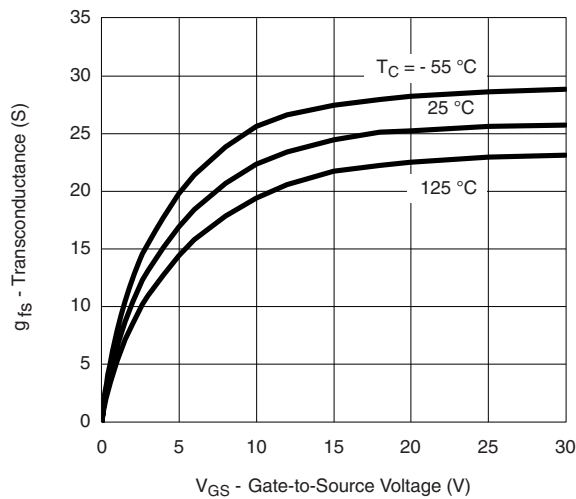
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



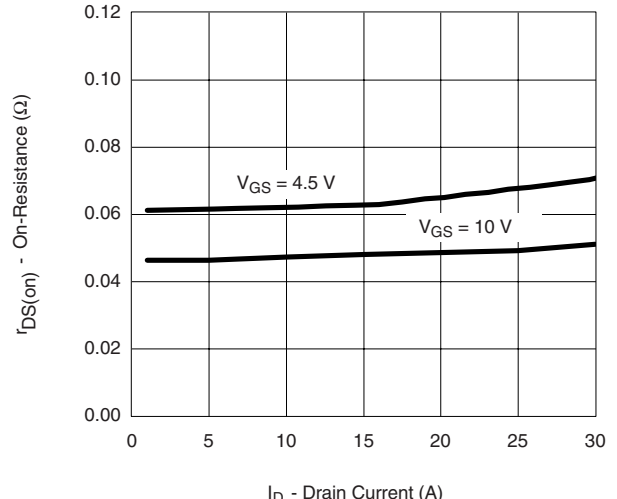
Output Characteristics



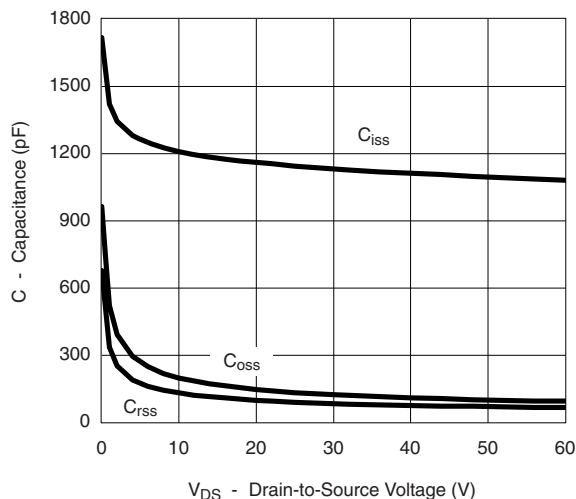
Transfer Characteristics



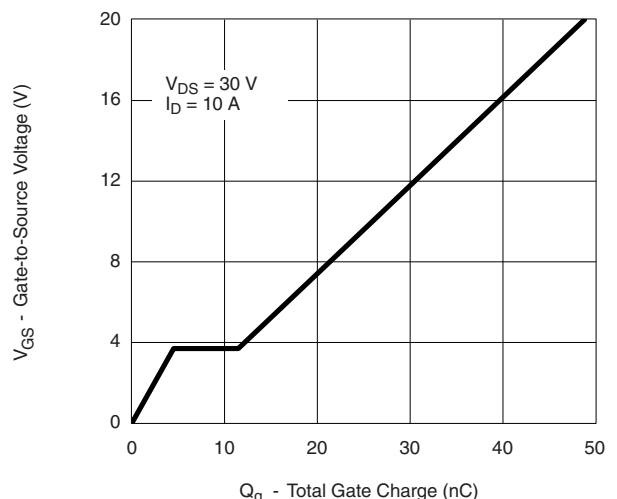
Transconductance



On-Resistance vs. Drain Current



Capacitance



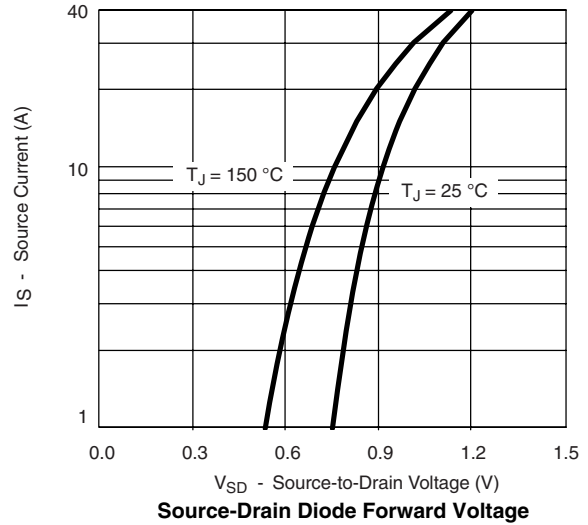
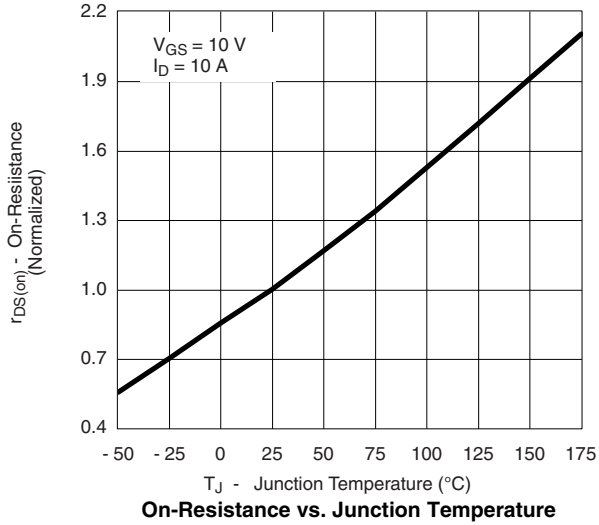
Gate Charge

SUD19P06-60L

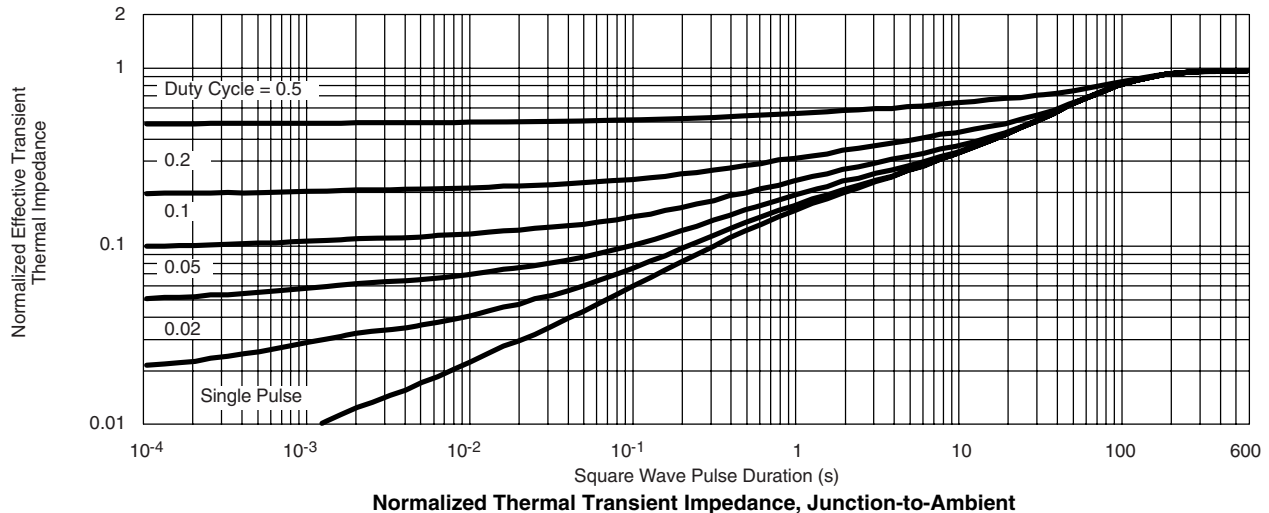
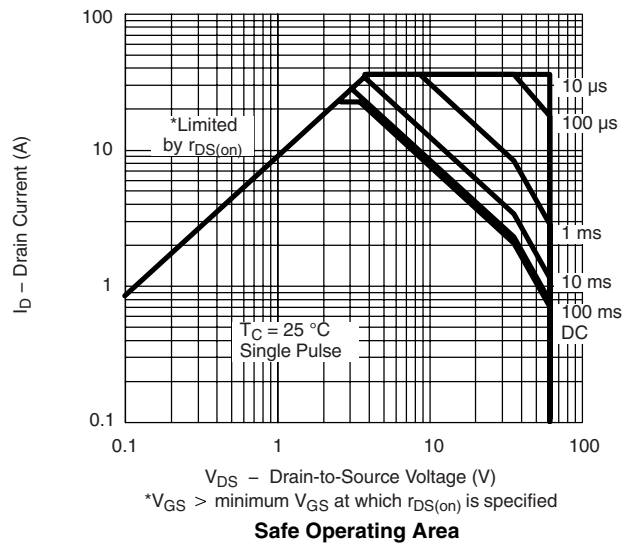
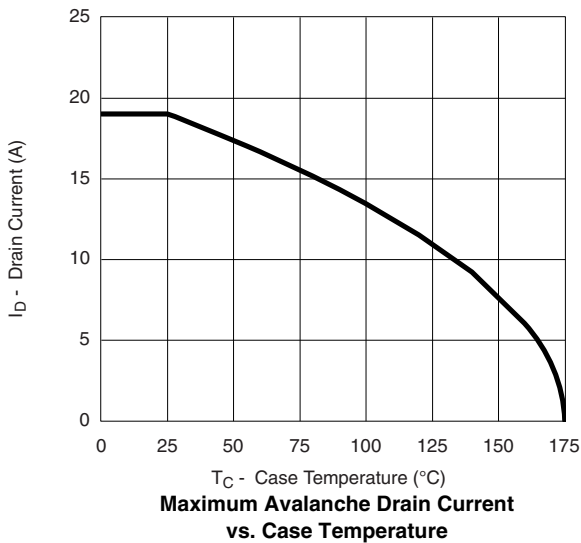


Vishay Siliconix

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

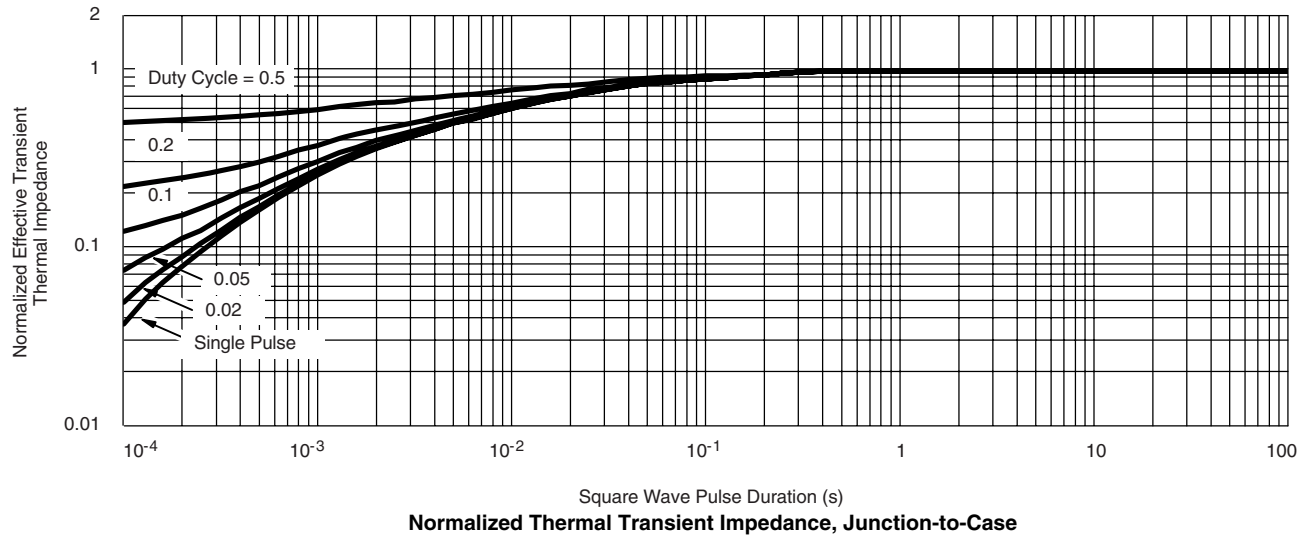


THERMAL RATINGS





THERMAL RATINGS



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?73103>



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- Подбор аналогов;
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- Техническая поддержка проекта;
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Как с нами связаться

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